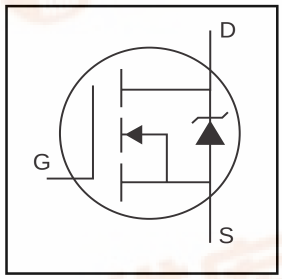
International
IOR Rectifier

PD - 94074

IRFZ48RS
IRFZ48RL

HEXFET® Power MOSFET

- Advanced Process Technology
- Dynamic dv/dt Rating
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Drop in Replacement of the IRFZ48 for Linear/Audio Applications



V_{DSS} = 60V

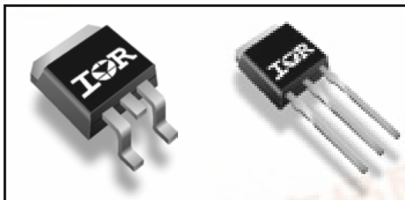
$R_{DS(on)}$ = 0.018Ω

I_D = 50*A

Description

Advanced HEXFET® Power MOSFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The D^2Pak is a surface mount power package capable of accommodating die sizes up to HEX-4. It provides the highest power capability and the lowest possible on-resistance in any existing surface mount package. The D^2Pak is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2.0W in a typical surface mount application.



D^2Pak IRFZ48RS   TO-262 IRFZ44RL

Absolute Maximum Ratings

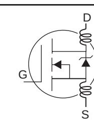
	Parameter	Max.	Units
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V	50*	A
I_D @ T_C = 100°C	Continuous Drain Current, V_{GS} @ 10V	50*	
I_{DM}	Pulsed Drain Current ①	290	
P_D @T_C = 25°C	Power Dissipation	190	W
	Linear Derating Factor	1.3	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy②	100	mJ
dv/dt	Peak Diode Recovery dv/dt ③	4.5	V/ns
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 175	°C
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	
	Mounting torque, 6-32 or M3 srew	10 lbf•in (1.1N•m)	

Thermal Resistance

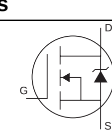
	Parameter	Typ.	Max.	Units
$R_{θJC}$	Junction-to-Case	——	0.8	°C/W
$R_{θCS}$	Case-to-Sink, Flat, Greased Surface	0.50	——	
$R_{θJA}$	Junction-to-Ambient	——	62	

05/21/02

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	60	——	——	V	V_{GS} = 0V, I_D = 250µA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	——	0.060	——	V/°C	Reference to 25°C, I_D = 1mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	——	——	0.018	Ω	V_{GS} = 10V, I_D = 43A ④
$V_{GS(th)}$	Gate Threshold Voltage	2.0	——	4.0	V	$V_{DS} = V_{GS}$, I_D = 250µA
g_{fs}	Forward Transconductance	27	——	——	S	V_{DS} = 25V, I_D = 43A④
I_{DSS}	Drain-to-Source Leakage Current	——	——	25	µA	V_{DS} = 60V, V_{GS} = 0V
		——	——	250		V_{DS} = 48V, V_{GS} = 0V, T_J = 150°C
I_{GSS}	Gate-to-Source Forward Leakage	——	——	100	nA	V_{GS} = 20V
	Gate-to-Source Reverse Leakage	——	——	-100		V_{GS} = -20V
Q_g	Total Gate Charge	——	——	110	nC	I_D = 72A
Q_{gs}	Gate-to-Source Charge	——	——	29		V_{DS} = 48V
Q_{gd}	Gate-to-Drain ("Miller") Charge	——	——	36		V_{GS} = 10V, See Fig. 6 and 13 ④
$t_{d(on)}$	Turn-On Delay Time	——	8.1	——	ns	V_{DD} = 30V
t_r	Rise Time	——	250	——		I_D = 72A
$t_{d(off)}$	Turn-Off Delay Time	——	210	——		R_G = 9.1Ω
t_f	Fall Time	——	250	——		R_D = 0.34Ω, See Fig. 10 ④
L_D	Internal Drain Inductance	——	4.5	——	nH	Between lead, 6mm (0.25in.)
L_S	Internal Source Inductance	——	7.5	——		from package and center of die contact 
C_{iss}	Input Capacitance	——	2400	——	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	——	1300	——		V_{DS} = 25V
C_{rss}	Reverse Transfer Capacitance	——	190	——		f = 1.0MHz, See Fig. 5

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	——	——	50*	A	MOSFET symbol showing the
I_{SM}	Pulsed Source Current (Body Diode)①	——	——	290		integral reverse p-n junction diode. 
V_{SD}	Diode Forward Voltage	——	——	2.0	V	T_J = 25°C, I_S = 72A, V_{GS} = 0V ④
t_{rr}	Reverse Recovery Time	——	120	180	ns	T_J = 25°C, I_F = 72A
Q_{rr}	Reverse Recovery Charge	——	0.50	0.80	µC	di/dt = 100A/µs ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

Notes:

① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)

② V_{DD} = 25V, Starting T_J = 25°C, L = 22µH R_G = 25Ω, I_{AS} = 72A. (See Figure 12)

③ $I_{SD} \leq$ 72A, di/dt ≤ 200A/µs, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq$ 175°C

④ Pulse width ≤ 300µs; duty cycle ≤ 2%.

* Current limited by the package, (Die Current = 72A)

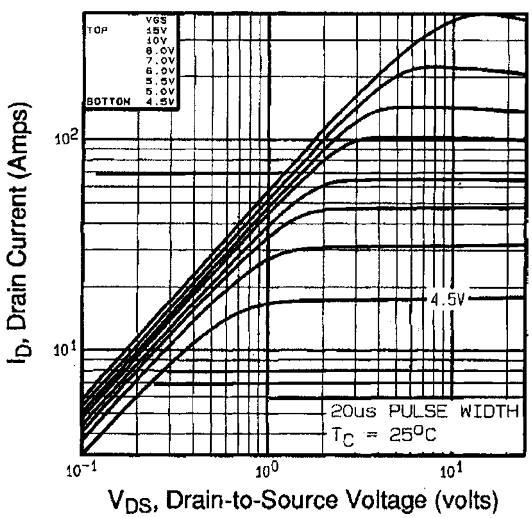


Fig 1. Typical Output Characteristics

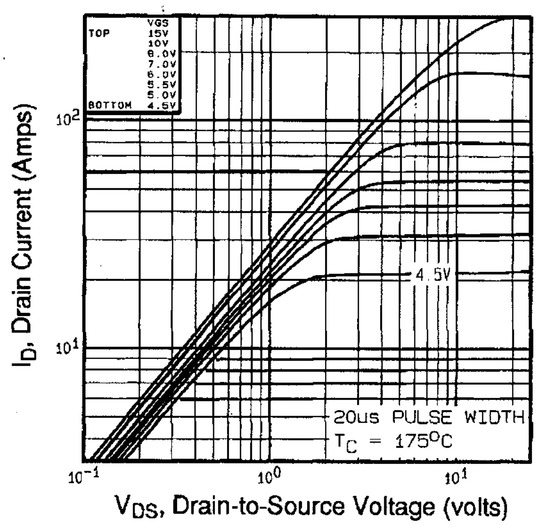


Fig 2. Typical Output Characteristics

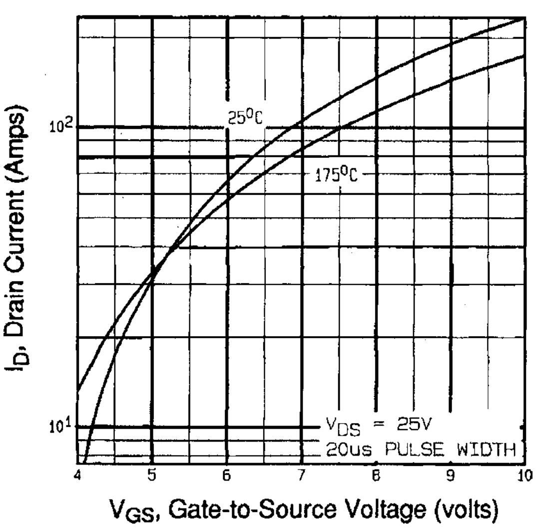


Fig 3. Typical Transfer Characteristics

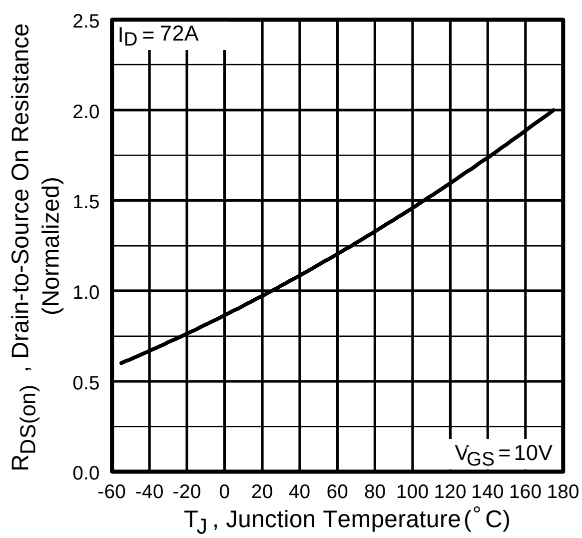


Fig 4. Normalized On-Resistance Vs. Temperature

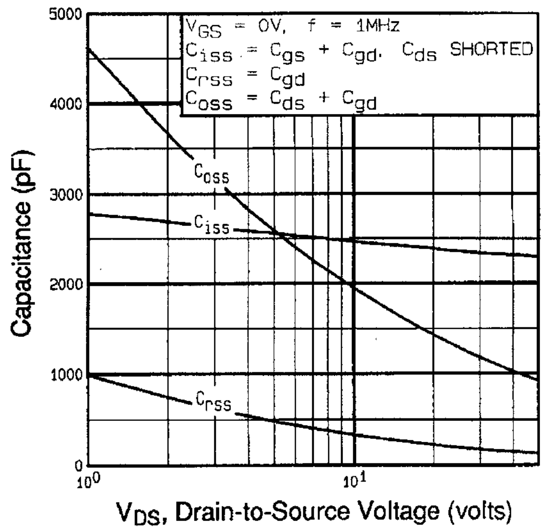


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

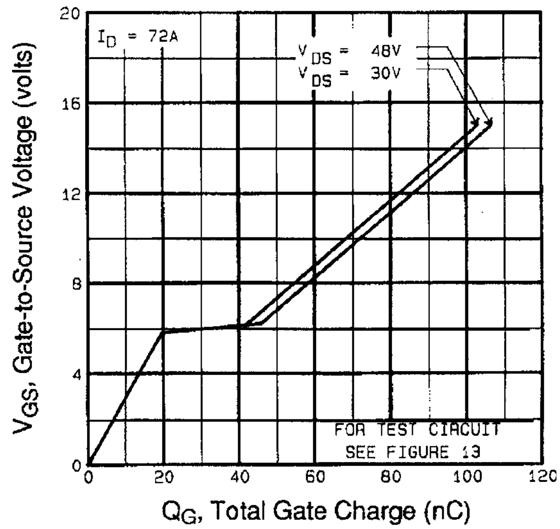


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

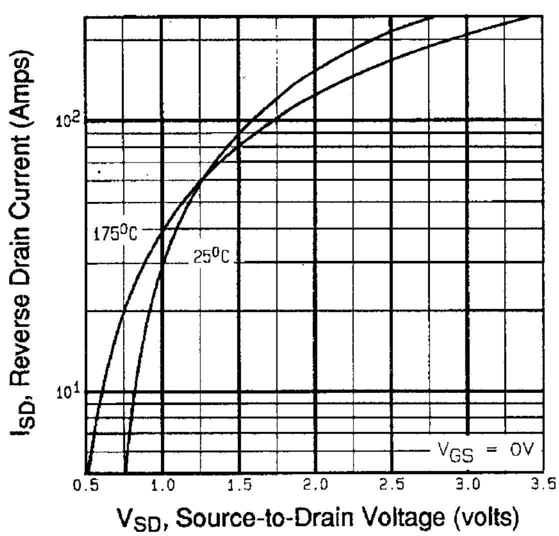


Fig 7. Typical Source-Drain Diode Forward Voltage

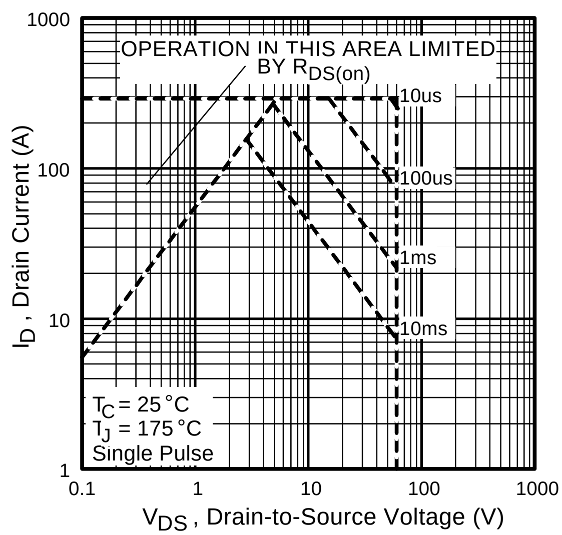


Fig 8. Maximum Safe Operating Area

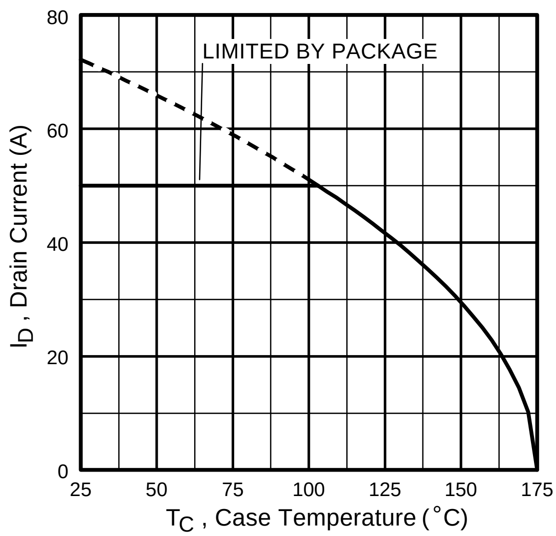


Fig 9. Maximum Drain Current Vs. Case Temperature

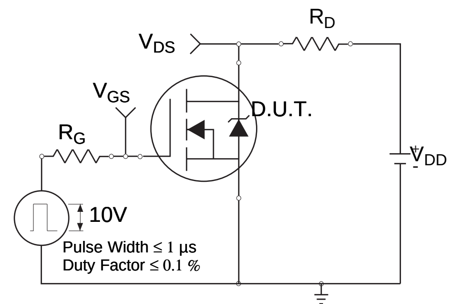


Fig 10a. Switching Time Test Circuit

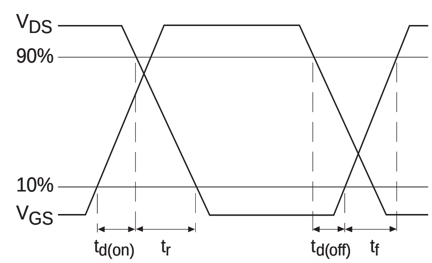


Fig 10b. Switching Time Waveforms

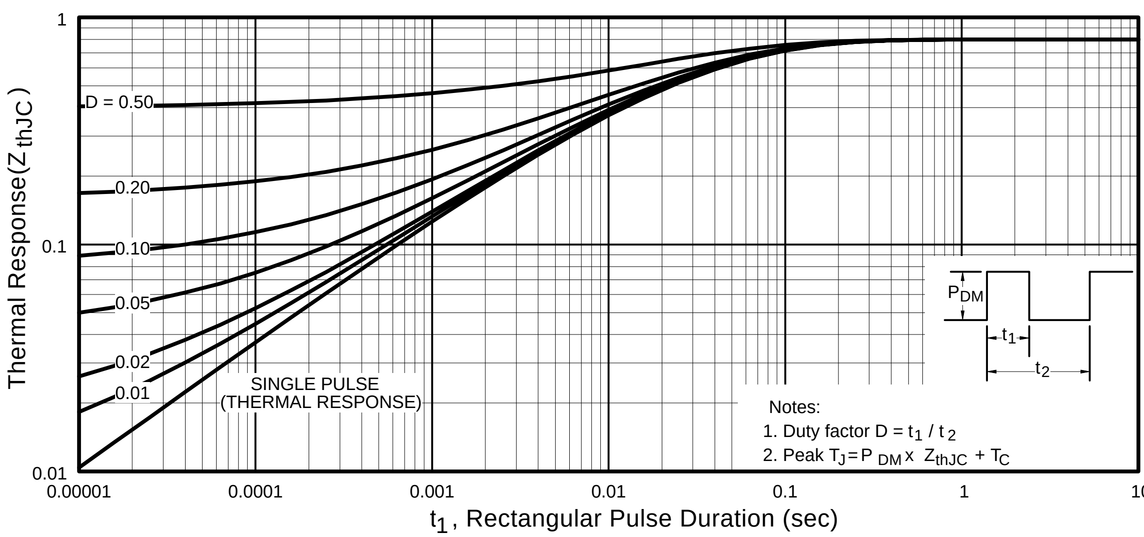


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

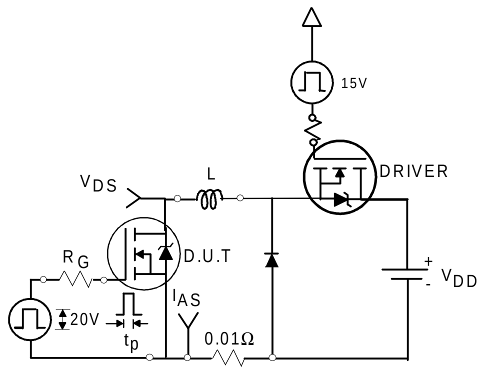


Fig 12a. Unclamped Inductive Test Circuit

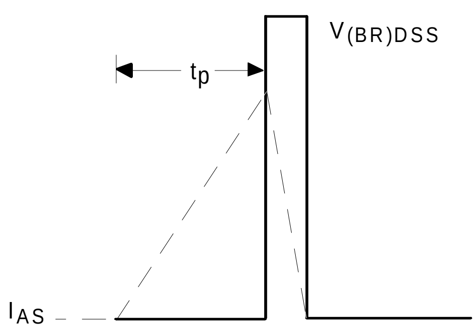


Fig 12b. Unclamped Inductive Waveforms

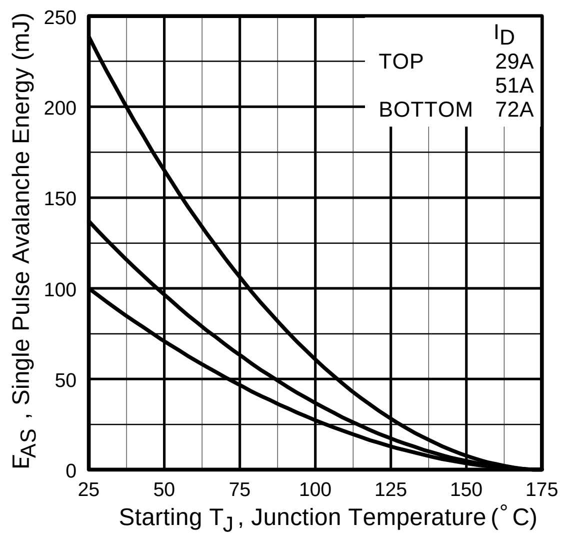


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

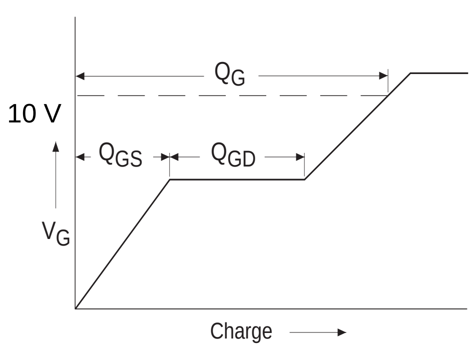


Fig 13a. Basic Gate Charge Waveform

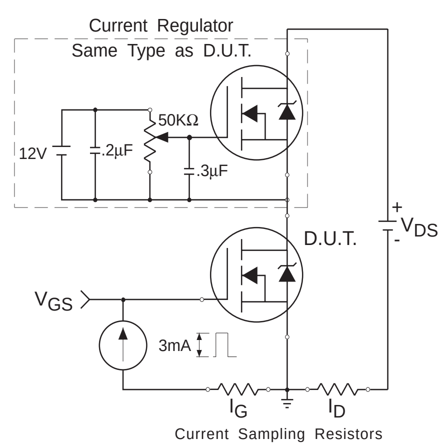
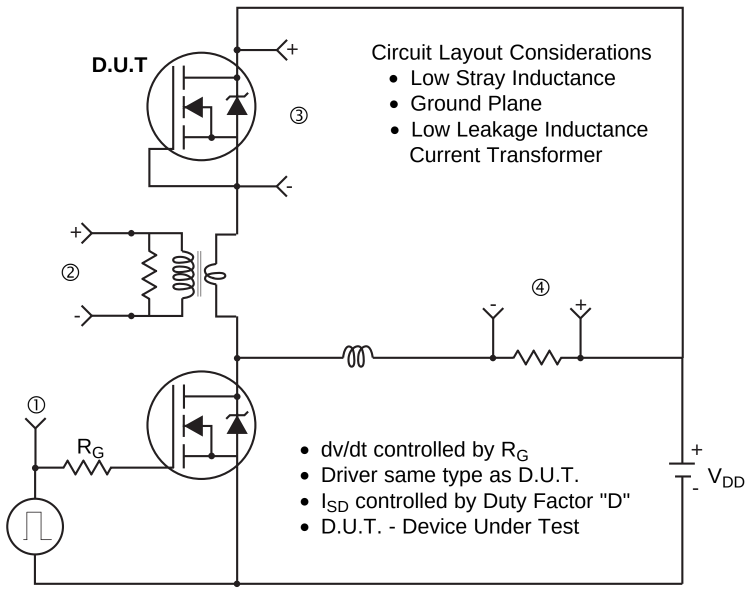


Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit



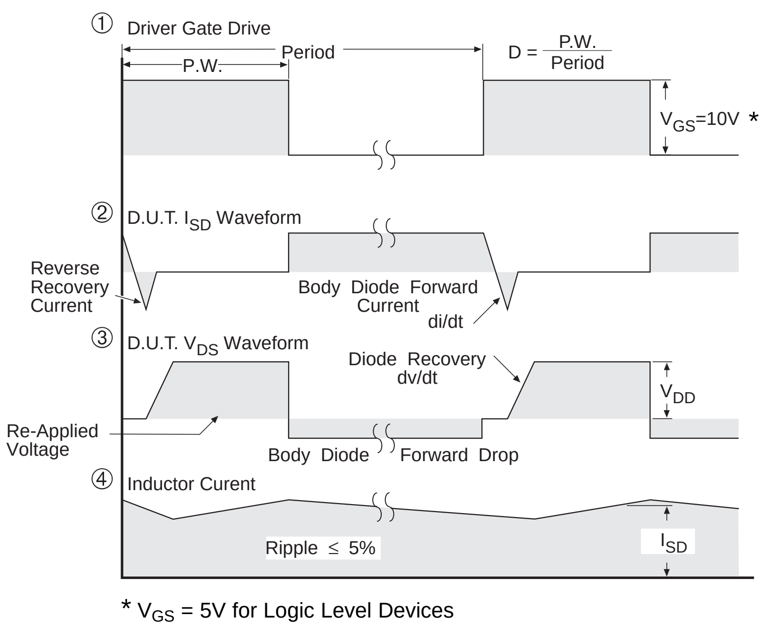
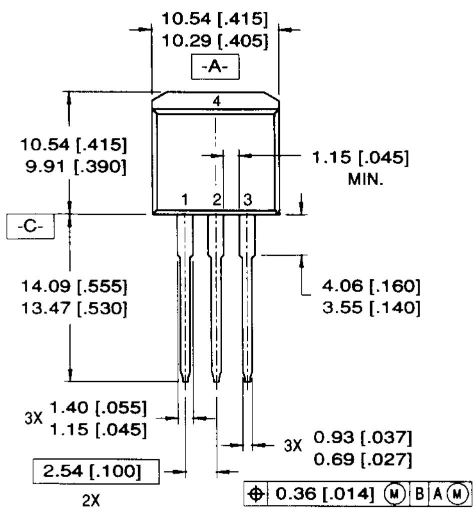
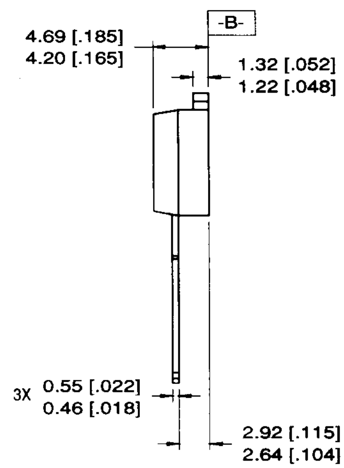


Fig 14. For N-Channel HEXFETS

TO-262 Package Outline





LEAD ASSIGNMENTS

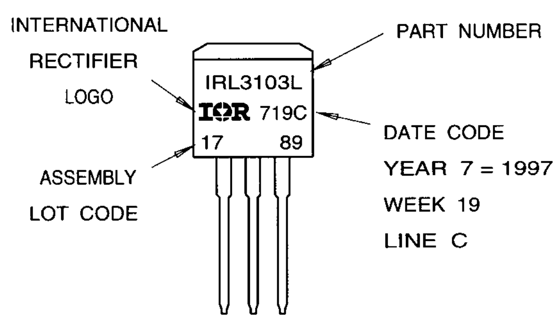
1 = GATE 3 = SOURCE
2 = DRAIN 4 = DRAIN

NOTES:

1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M-1982
2. CONTROLLING DIMENSION: INCH.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. HEATSINK & LEAD DIMENSIONS DO NOT INCLUDE BURRS.

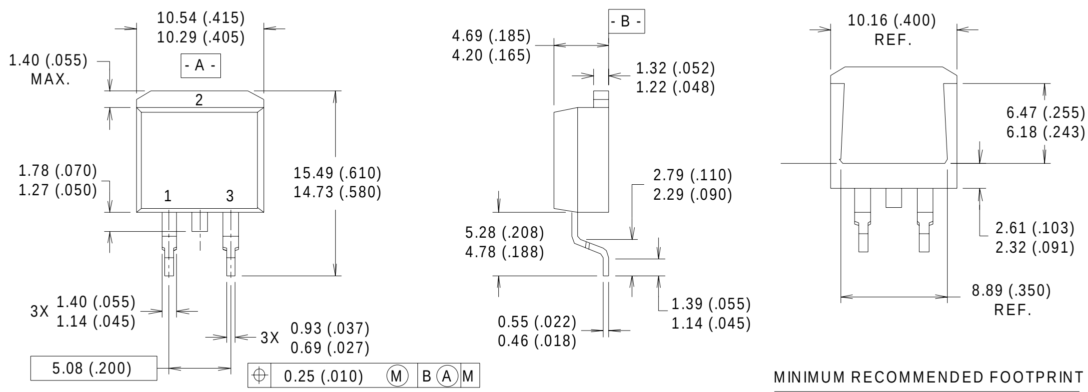
TO-262 Part Marking Information

EXAMPLE: THIS IS AN IRL3103L
LOT CODE 1789
ASSEMBLED ON WW 19, 1997
IN THE ASSEMBLY LINE "C"

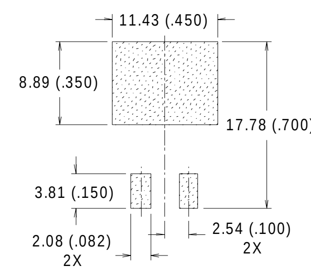


D²Pak Package Outline

Dimensions are shown in millimeters (inches)



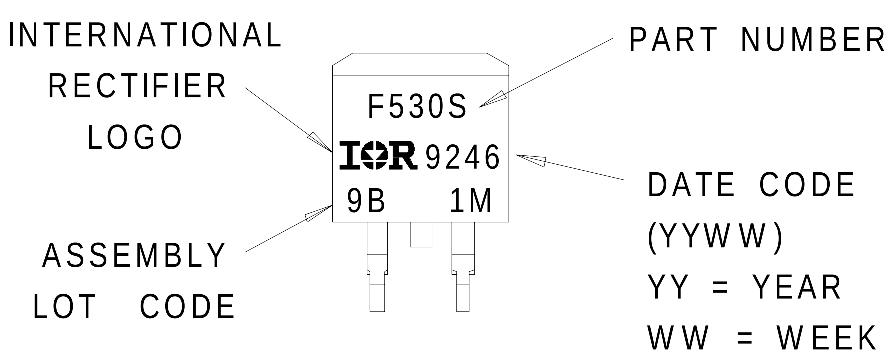
MINIMUM RECOMMENDED FOOTPRINT



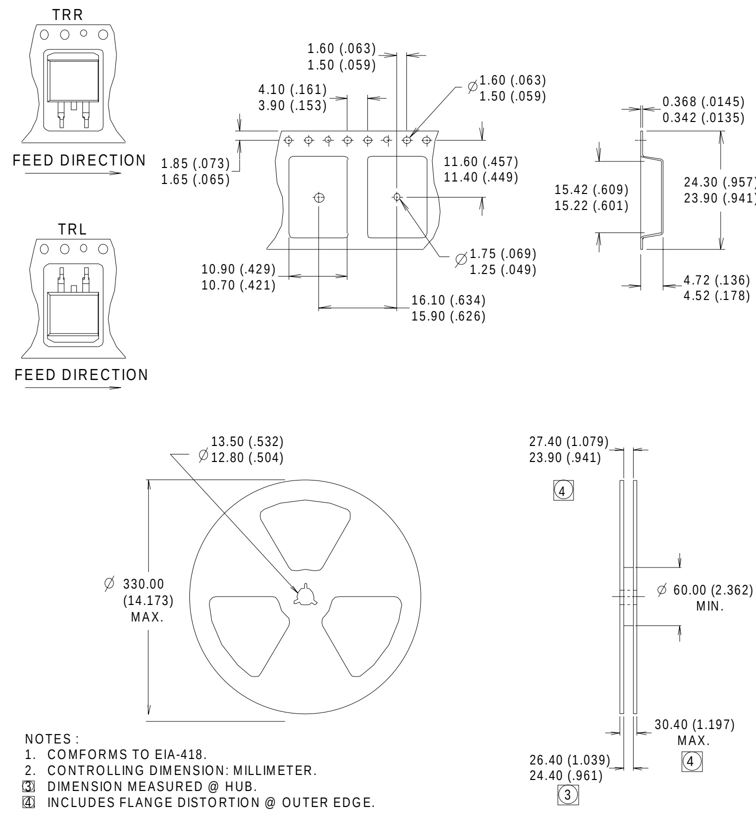
NOTES:
1 DIMENSIONS AFTER SOLDER DIP.
2 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
3 CONTROLLING DIMENSION : INCH.
4 HEATSINK & LEAD DIMENSIONS DO NOT INCLUDE BURRS.

LEAD ASSIGNMENTS
1 - GATE
2 - DRAIN
3 - SOURCE

D²Pak Part Marking Information



D²Pak Tape & Reel Information



Data and specifications subject to change without notice.
This product has been designed and qualified for the Industrial market.
Qualification Standards can be found on IR's Web site.

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